

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS} = 100V, I_D = 240A$
 $R_{DS(ON)} = 2.0m\Omega$, typical (TO-220)@ $V_{GS} = 10V$
 $R_{DS(ON)} = 1.8m\Omega$, typical (TO-263)@ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

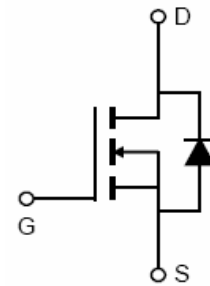
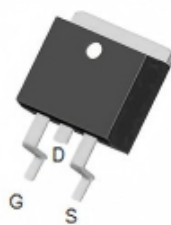
100% UIS TESTED!

100% ΔV_{ds} TESTED!

TO-220



TO-263



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
RSTP023N10	RSTP023N10	TO-220	-	-	-
RSTP023N10D	RSTP023N10D	TO-263	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	240	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D (100^\circ C)$	170	A
Pulsed Drain Current (Note 1)	I_{DM}	960	A
Maximum Power Dissipation	P_D	340	W
Derating factor		2.27	W/ $^\circ C$
Single pulse avalanche energy (Note 4)	E_{AS}	2784	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	0.44	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	60	$^{\circ}\text{C/W}$

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100		-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics ^(Note 2)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =120A	TO-220	-	2.0	2.3	mΩ
			TO-263		1.8	2.1	mΩ
Gate resistance	R _G		-	2.5	-	Ω	
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =120A		200	-	S	
Dynamic Characteristics ^(Note3)							
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz	-	17000	-	PF	
Output Capacitance	C _{oss}		-	1500	-	PF	
Reverse Transfer Capacitance	C _{rss}		-	77	-	PF	
Switching Characteristics ^(Note 3)							
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V,I _D =120A V _{GS} =10V,R _G =1.6Ω	-	37	-	nS	
Turn-on Rise Time	t _r		-	29	-	nS	
Turn-Off Delay Time	t _{d(off)}		-	82	-	nS	
Turn-Off Fall Time	t _f		-	34	-	nS	
Total Gate Charge	Q _g	V _{DS} =50V,I _D =120A, V _{GS} =10V	-	252	-	nC	
Gate-Source Charge	Q _{gs}		-	72		nC	
Gate-Drain Charge	Q _{gd}		-	63		nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =120A	-		1.2	V	
Diode Forward Current ^(Note 2)	I _S		-	-	240	A	
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 120A di/dt = 100A/μs ^(Note2)	-	105	-	nS	
Reverse Recovery Charge	Q _{rr}		-	290	-	nC	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^{\circ}\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on .the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.
3. Guaranteed by design, not subject to production
4. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_G=25\Omega$

Typical Electrical and Thermal Characteristics

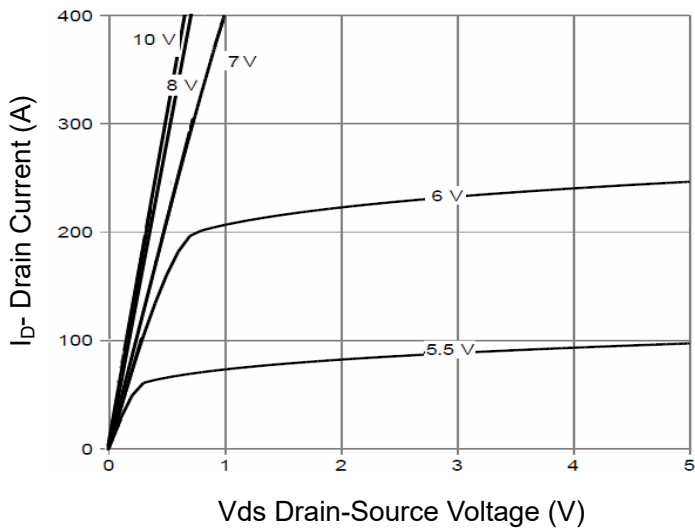


Figure 1 Output Characteristics

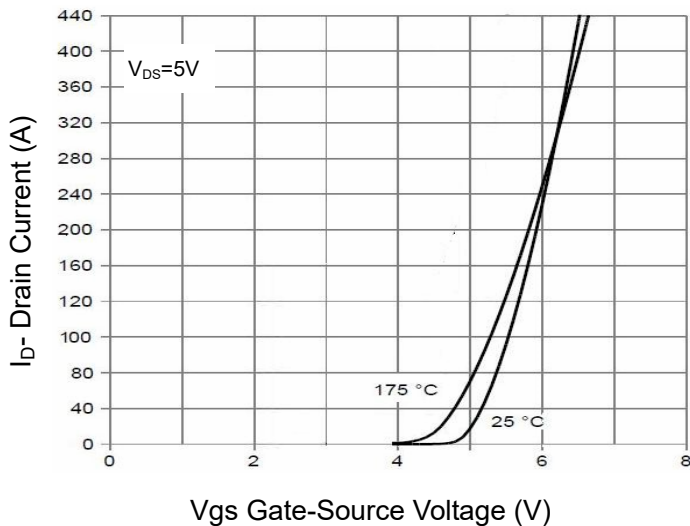


Figure 2 Transfer Characteristics

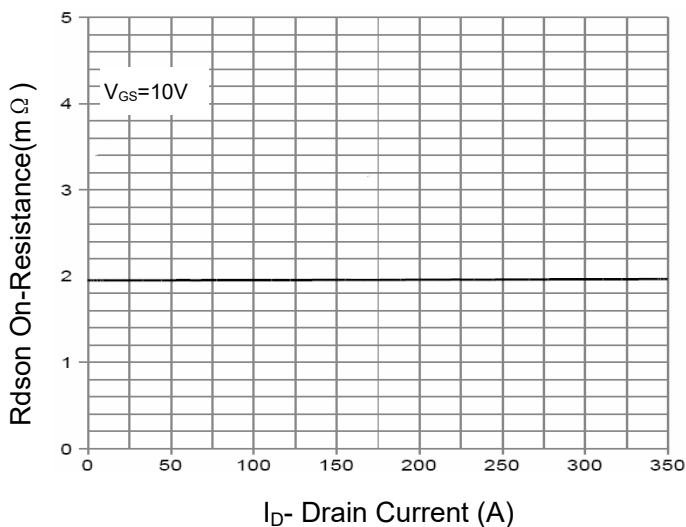


Figure 3 $R_{DS(on)}$ - Drain Current

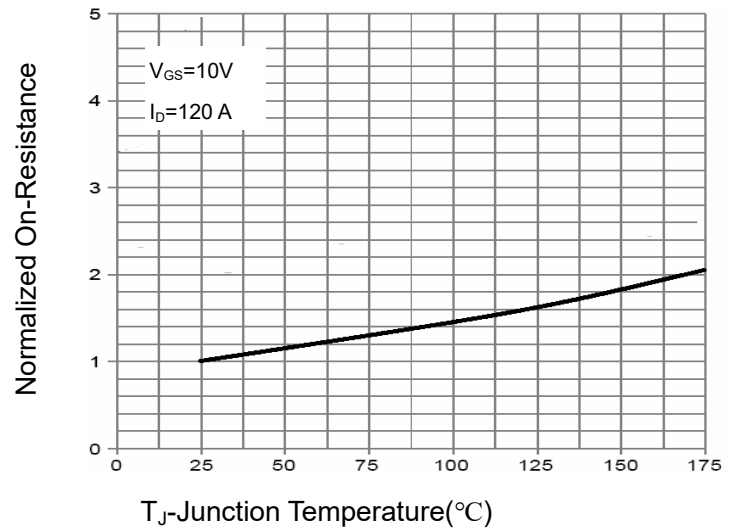


Figure 4 $R_{DS(on)}$ -Junction Temperature

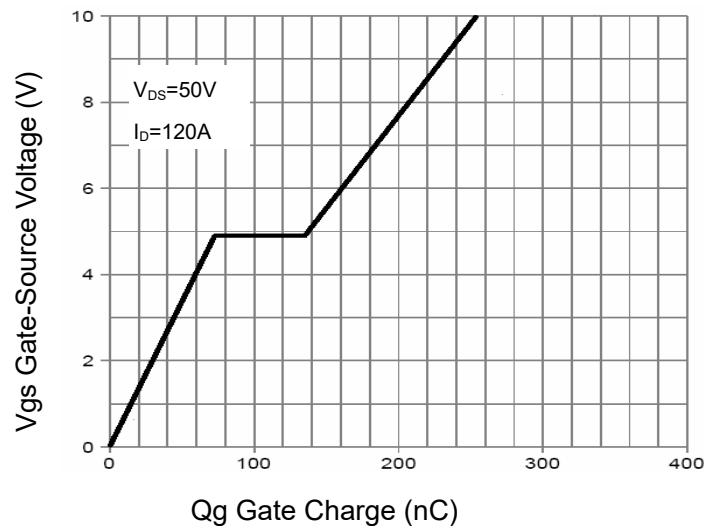


Figure 5 Gate Charge

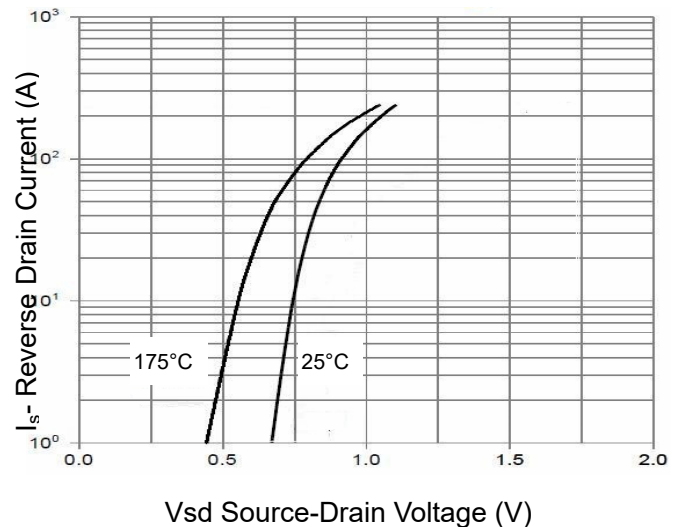
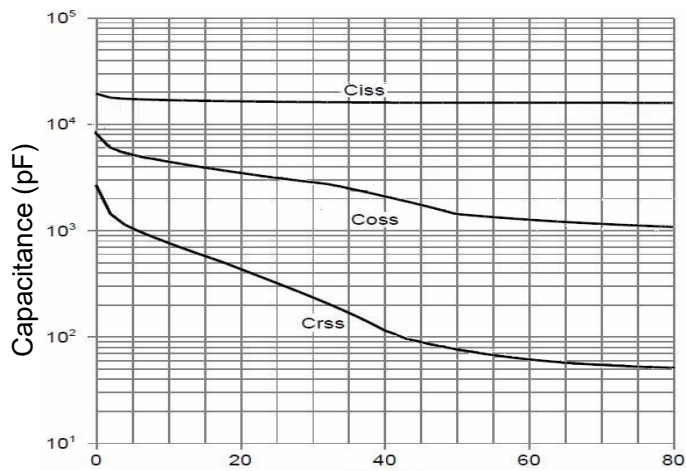
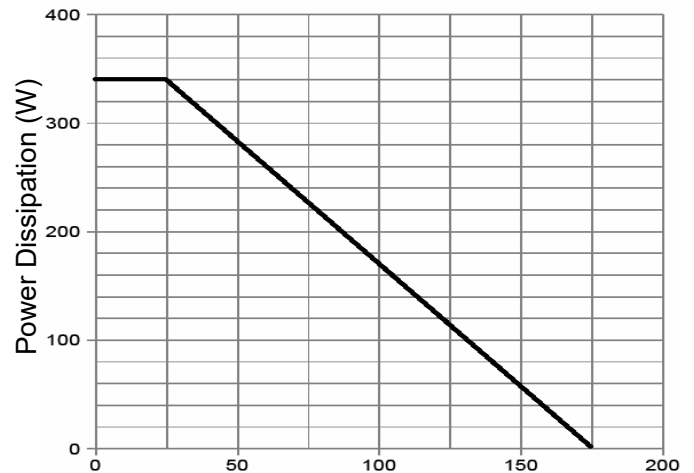


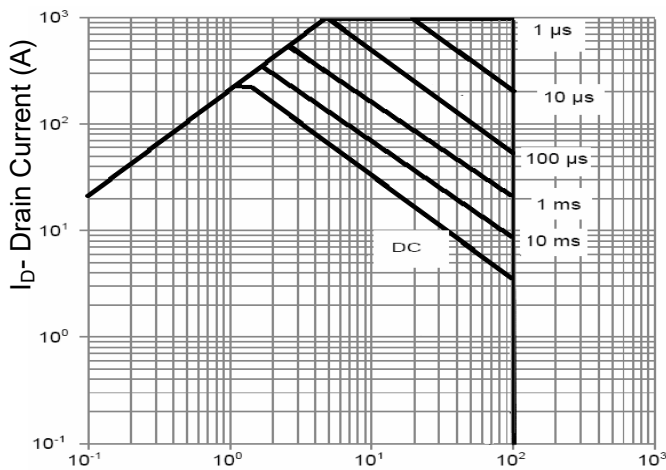
Figure 6 Source- Drain Diode Forward



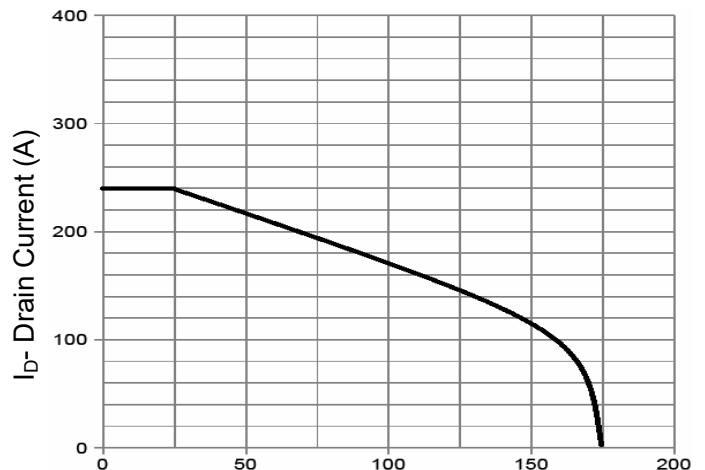
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



TJ-Junction Temperature(°C)
Figure 9 Power De-rating



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



TJ-Junction Temperature (°C)
Figure 10 Current De-rating

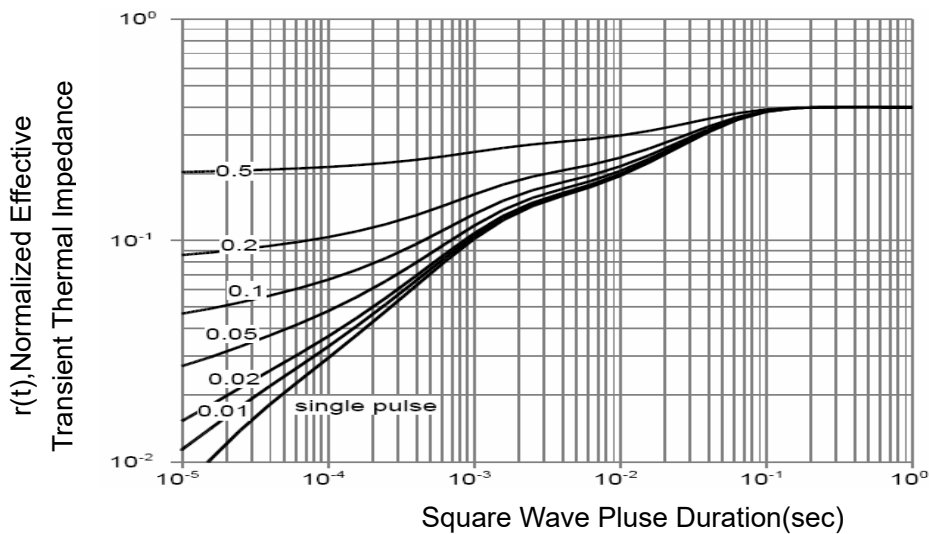
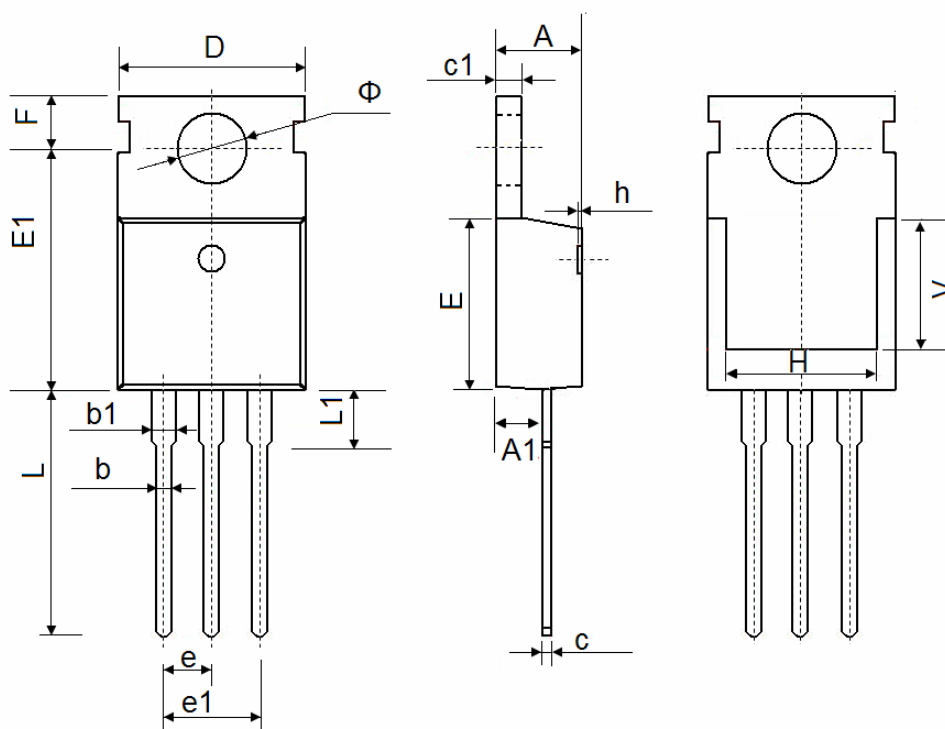


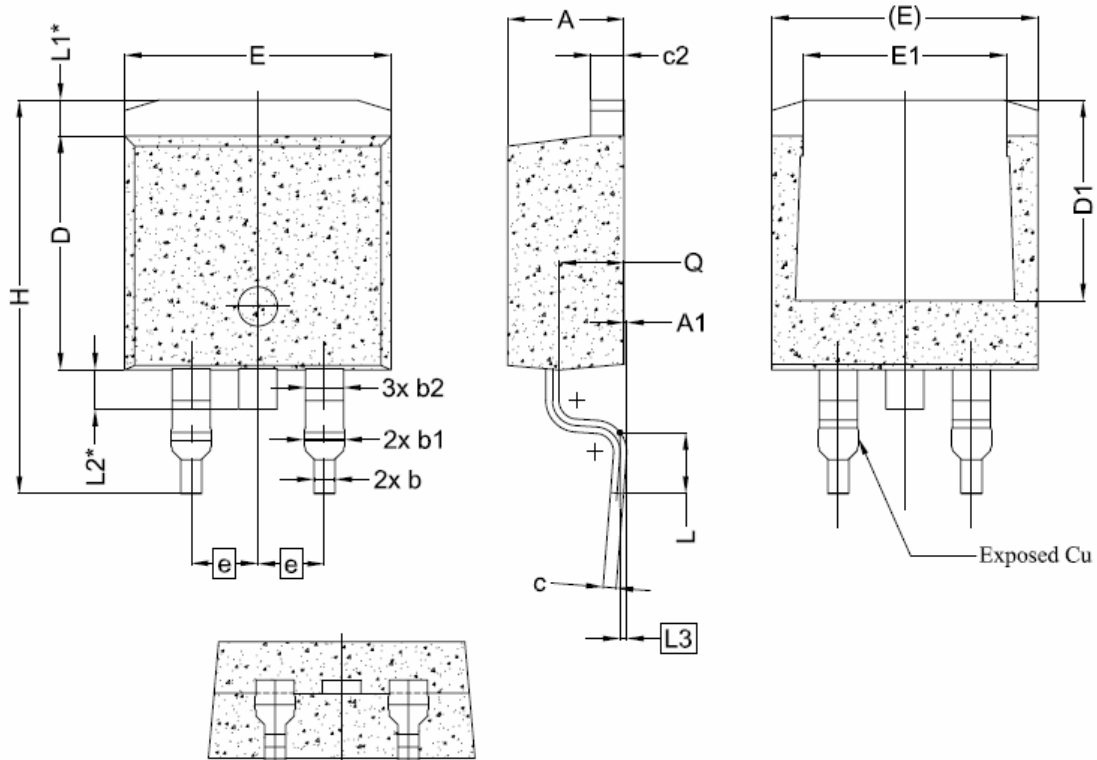
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150

TO-263-2L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	-
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

